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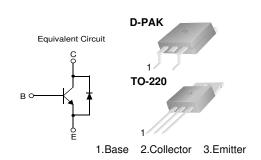


December 2009

KSC5402D/KSC5402DT NPN Silicon Transistor, Planar Silicon Transistor

Features

- · High Voltage High Speed Power Switch Application
- · Wide Safe Operating Area
- · Built-in Free Wheeling Diode
- · Suitable for Electronic Ballast Application
- · Small Variance in Storage Time
- Two Package Choices; D-PAK or TO-220



Absolute Maximum Ratings T_A=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|-------------|--------|
| V _{CBO} | Collector-Base Voltage | 1000 | V |
| V _{CEO} | Collector-Emitter Voltage | 450 | V |
| V _{EBO} | Emitter-Base Voltage | 12 | V |
| I _C | Collector Current (DC) | 2 | Α |
| I _{CP} | *Collector Current (Pulse) | 5 | Α |
| I _B | Base Current (DC) | 1 | Α |
| I _{BP} | *Base Current (Pulse) | 2 | Α |
| P _C | Power Dissipation(T _C =25°C) : D-PAK* : TO-220 | 30 50 | W W |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 65 to 150 | °C |

^{*} Pulse Test: Pulse Width=5ms, Duty Cycle≤10%

Thermal Characteristics T_A=25°C unless otherwise noted

| Symbol | Parameter | | Rat | Units | |
|-----------------|---|---------------------|--------|-------|------|
| | | | TO-220 | D-PAK | |
| $R_{	heta JC}$ | Thermal Resistance | Junction to Case | 2.5 | 4.17* | °C/W |
| $R_{\theta JA}$ | | Junction to Ambient | 62.5 | 50 | °C/W |
| TL | Maximum Lead Temperature for Soldering Purpose ; 1/8" from Case for 5 Seconds | | 270 | 270 | °C |

^{*} Mounted on 1" square PCB (FR4 ro G-10 Material)

Electrical Characteristics T_A =25°C unless otherwise noted

| Symbol | Parameter | Test Condition | | Min. | Тур. | Max. | Units |
|-----------------------|---|---|--|------|------|------|-------|
| BV _{CBO} | Collector-Base Breakdown Voltage | I _C =1mA, I _E =0 | | 1000 | 1090 | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C =5mA, I _B =0 | | 450 | 525 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | I _E =1mA, I _C =0 | I _E =1mA, I _C =0 | | 14 | | V |
| I _{CES} | Collector Cut-off Current | V _{CES} =1000V, I _{EB} =0 | T _A =25°C | | 0.03 | 100 | μΑ |
| | | | T _A =125°C | | 1.2 | 500 | μΑ |
| I _{CEO} | Collector Cut-off Current | V_{CE} =450V, V_{B} =0 | T _A =25°C | | 0.3 | 100 | μΑ |
| | | | T _A =125°C | | 15 | 500 | μΑ |
| I _{EBO} | Emitter Cut-off Current | V _{EB} =10V, I _C =0 | | | 0.01 | 100 | μΑ |
| h _{FE} | DC Current Gain | V _{CE} =1V, I _C =0.4A | T _A =25°C | 14 | 29 | | |
| | | | T _A =125°C | 8 | 17 | | |
| | | V _{CE} =1V, I _C =1A | T _A =25°C | 6 | 9 | | |
| | | | T _A =125°C | 4 | 6 | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C =0.4, I _B =0.04A | T _A =25°C | | 0.25 | 0.6 | V |
| | | | T _A =125°C | | 0.4 | 1.0 | V |
| | | I _C =1A, I _B =0.2A | T _A =25°C | | 0.3 | 0.75 | V |
| | | | T _A =125°C | | 0.65 | 1.2 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C =0.4A, I _B =0.04A | T _A =25°C | | 0.78 | 1.0 | V |
| | | | T _A =125°C | | 0.65 | 0.9 | V |
| | | | T _A =25°C | | 0.85 | 1.1 | V |
| | | | T _A =125°C | | 0.75 | 1.0 | V |
| C _{ib} | Input Capacitance | V _{EB} =8V, I _C =0, f=1MHz | | | 330 | 500 | pF |
| C _{ob} | Output Capacitance | V _{CB} =10V, I _E =0, f=1MHz | | | 35 | 100 | pF |
| f _T | Current Gain Bandwidth Product | I _C =0.5A, V _{CE} =10V | | | 11 | | MHz |
| V _F | Diode Forward Voltage | I _F =1A | T _A =25°C | | 0.86 | 1.5 | V |
| | | I _F =0.2A | T _A =25°C | | 0.75 | 1.2 | V |
| | | | T _A =125°C | | 0.6 | | V |
| | | I _F =0.4A | T _A =25°C | | 0.8 | 1.3 | V |
| | | | T _A =125°C | | 0.65 | | V |

| Symbol | Parameter | Test Condition | | Min. | Тур. | Max. | Units |
|------------------------|---|---|-----------------------|------|-------------------|------|----------------|
| t _{fr} | Diode Froward Recvery Time (di/dt=10A/μs) | I _F =0.2A I _F =0.4A I _F =1A | | | 540 520 480 | | ns ns ns |
| V _{CE} (DSAT) | Dynamic Saturation Voltage | I _C =0.4A, I _{B1} =40mA V _{CC} =300V | @ 1μs | | 7.5 | | V |
| | | | @ 3μs | | 2.5 | | V |
| | | I _C =1A, I _{B1} =200mA V _{CC} =300 | @ 1μs | | 11.5 | | V |
| | | | @ 3μs | | 1.5 | | V |
| RESISTIVE | LOAD SWITCHING (D.C \leq 10%, F | Pulse Width=20µs) | | | | | |
| t _{ON} | Turn On Time | I _C =1A, | T _A =25°C | | 110 | 150 | ns |
| | | I _{B1} =200mA, I _{B2} =150mA, | T _A =125°C | | 135 | | ns |
| t _{OFF} | Turn Off Time | V _{CC} =300V, | T _A =25°C | 0.95 | | 1.25 | μS |
| | | $R_{\rm L} = 300\Omega$ | T _A =125°C | | 1.4 | | μS |
| INDUCTIVE | LOAD SWITCHING (V _{CC} =15V) | | • | | | • | • |
| t _{STG} | Storage Time | $\begin{array}{l} I_{C}{=}0.4\text{A}, \\ I_{B1}{=}40\text{mA}, \\ I_{B2}{=}200\text{mA}, \\ \text{Vz}{=}300\text{V}, \\ L_{C}{=}200\text{H} \end{array}$ | T _A =25°C | | 0.56 | 0.65 | μS |
| | | | T _A =125°C | | 0.7 | | μS |
| t _F | Fall Time | | T _A =25°C | | 60 | 175 | ns |
| | | | T _A =125°C | | 75 | | ns |
| t _C | Cross-over Time | | T _A =25°C | | 90 | 175 | ns |
| | | | T _A =125°C | | 90 | | ns |
| t _{STG} | Storage Time | I _C =0.8A, I _{B1} =160mA, | T _A =25°C | | | 2.75 | μS |
| | | | T _A =125°C | | 3 | | μS |
| t _F | Fall Time | I _{B2} =160mA, Vz=300V, | T _A =25°C | | 110 | 175 | ns |
| | | L _C =200H | T _A =125°C | | 180 | | ns |
| t _C | Cross-over Time | | T _A =25°C | | 125 | 350 | ns |
| | | | T _A =125°C | | 185 | | ns |
| t _{STG} | t _{STG} Storage Time t _F Fall Time | $\begin{array}{c} I_{C}{=}1A, \\ I_{B1}{=}200\text{mA}, \\ I_{B2}{=}500\text{mA}, \\ V_{Z}{=}300\text{V}, \\ L_{C}{=}200\mu\text{H} \end{array}$ | T _A =25°C | | 1.1 | 1.2 | μS |
| | | | T _A =125°C | | 1.35 | | μS |
| t_{F} | | | T _A =25°C | | 105 | 150 | ns |
| | | | T _A =125°C | | 75 | | ns |
| t_{C} | Cross-over Time | | T _A =25°C | | 125 | 150 | ns |
| | | | T _A =125°C | | 100 | | ns |

Typical Performance Characteristics

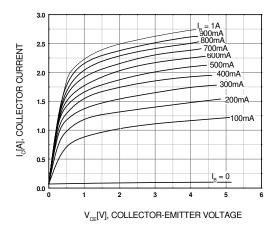


Figure 1. Static Characteristic

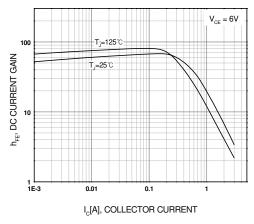


Figure 3. DC current Gain

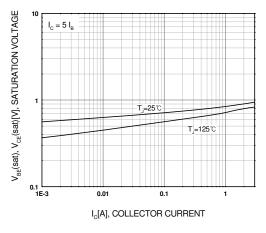


Figure 5. Base-Emitter Saturation Voltage

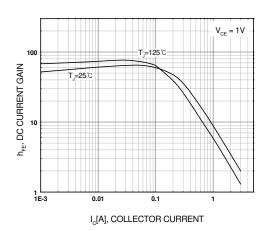


Figure 2. DC current Gain

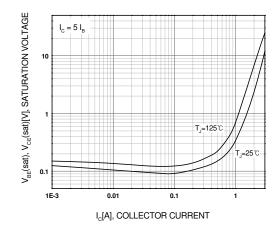


Figure 4. Collector-Emitter Saturation Voltage

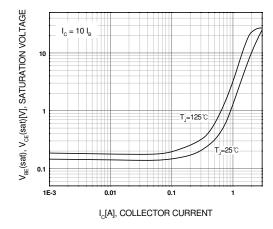


Figure 6. Collector-Emitter Saturation Voltage

Typical Performance Characteristics (Continued)

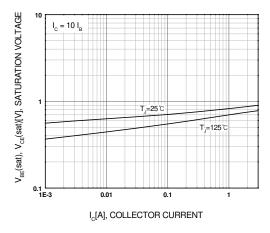


Figure 7. Base-Emitter Saturation Voltage

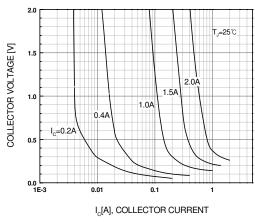


Figure 9. Typical Collector Saturation Region

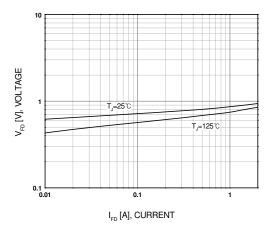


Figure 11. Diode Forward Voltage

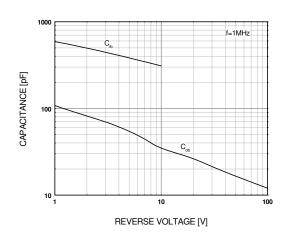


Figure 8. Collector Output Capacitance

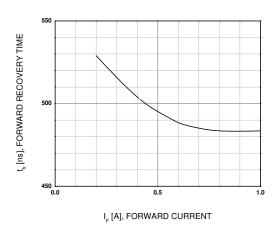


Figure 10. Forward Recovery Time

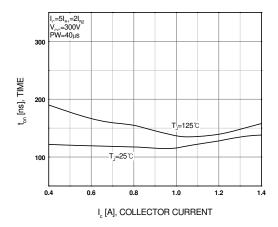


Figure 12. Resistive Switching Time, ton

Typical Performance Characteristics (Continued)

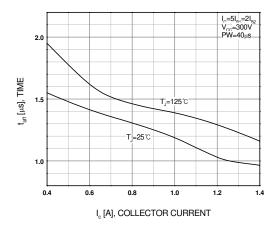


Figure 13. Resistive Switching Time, toff

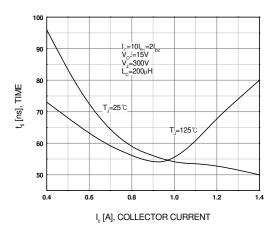


Figure 15. Inductive Switching Time, tfi

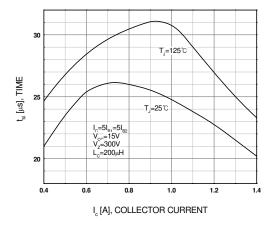


Figure 17. Inductive Switching Time, tsi

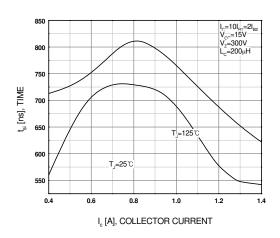


Figure 14. Inductive Switching Time, tsi

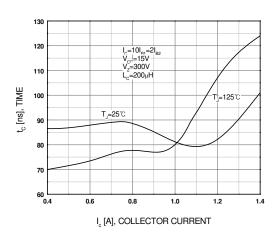


Figure 16. Inductive Switching Time, t_c

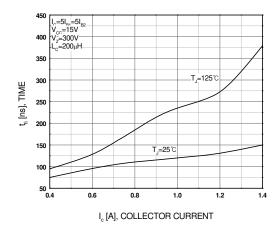


Figure 18. Inductive Switching Time, tfi

Typical Performance Characteristics (Continued)

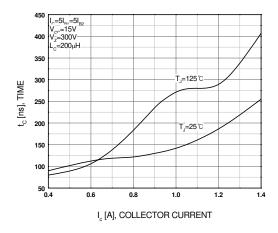


Figure 19. Inductive Switching Time, t_c

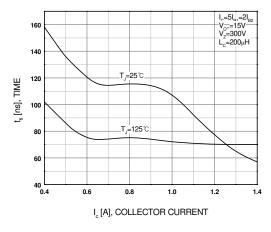


Figure 21. Inductive Switching Time, tfi

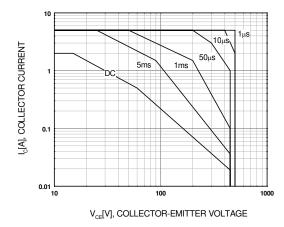


Figure 23. Forward Bias Safe Operating Area

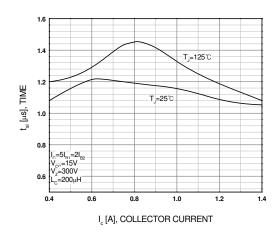


Figure 20. Inductive Switching Time, tsi

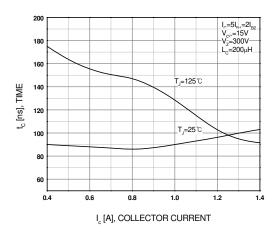


Figure 22. Inductive Switching Time, t_c

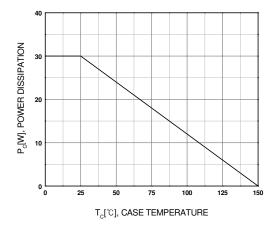
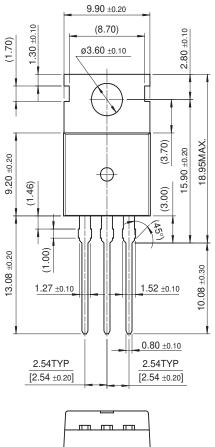
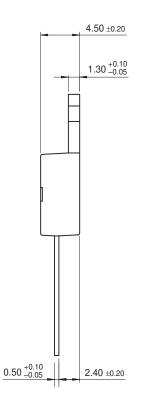


Figure 24. Power Derating

Physical Dimension

TO-220



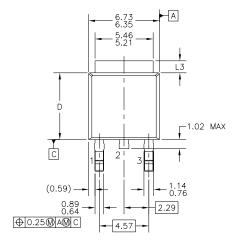


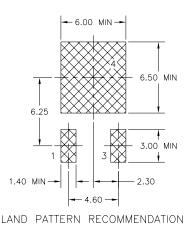
10.00 ±0.20

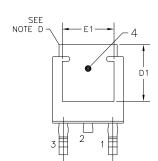
Dimensions in Millimeters

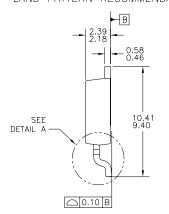
Physical Dimension (Continued)

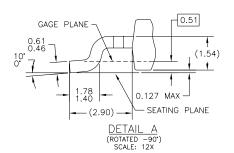
D-PAK











- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.

 B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.

 C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

 D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.

 E) DIMENSIONS L3.D.E1&D1 TABLE:

D 5.97-6.22 5.33-5.56 E1 4.32 MIN 3.81 MIN D1 5.21 MIN 4.57 MIN PRESENCE OF TRIMMED CI IS OPTIONAL. TRIMMED CENTER LEAD

Dimensions in Millimeters





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|--------------------------|-----------------------|---|--|--|--|
| Datasheet Identification | | Definition | | | |
| Advance Information | Formative / In Design | Datasheet contains the design specifications for product development. Specifications may change in any manner without notice. | | | |
| Preliminary | First Production | Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. | | | |
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